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(54) Title (EN): P-I-N PHOTODETECTOR

(54) Title (FR): PHOTODÉTECTEUR P-I-N

(57) Abstract:

(EN): A photodetector which comprises a measurement layer (15) and at least a first photoactive layer (11) which covers the measurement layer (15). The measurement layer (15) may be a transistor channel or a charge accumulation electrode. The conductivity type of the measurement layer is n-type, p-type or ambipolar and the first photoactive layer (11) exhibits intrinsic semiconductivity.

(FR): La présente invention concerne un photodétecteur qui comprend une couche de mesure (15) et au moins une première couche photoactive (11) qui recouvre la couche de mesure (15). La couche de mesure (15) peut être un canal de transistor ou une électrode d'accumulation de charge. Le type de conductivité de la couche de mesure est de type n, de type p ou ambipolaire et la première couche photoactive (11) présente une semi-conductivité intrinsèque.

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